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HUANG et al.(10) **Pub. No.: US 2023/0230839 A1**(43) **Pub. Date: Jul. 20, 2023**(54) **METHOD FOR ION IMPLANTATION THAT
ADJUSTS A TARGET'S TILT ANGLE BASED
ON A DISTRIBUTION OF EJECTED IONS
FROM A TARGET**division of application No. 16/381,863, filed on Apr.
11, 2019, now Pat. No. 11,195,720.(60) Provisional application No. 62/752,268, filed on Oct.
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(TW)(21) Appl. No.: **18/126,861**(22) Filed: **Mar. 27, 2023****Related U.S. Application Data**(60) Continuation of application No. 17/529,504, filed on
Nov. 18, 2021, now Pat. No. 11,615,961, which is a(57) **ABSTRACT**

The present disclosure describes a system and a method for an ion implantation (IMP) process. The system includes an ion implanter configured to scan an ion beam over a target for a range of angles, a tilting mechanism configured to support and tilt the target, an ion-collecting device configured to collect a distribution and a number of ejected ions from the ion beam scan over the target, and a control unit configured to adjust a tilt angle based on a correction angle determined based on the distribution and number of ejected ions.

